



MFO/M-300

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Richard A. Blanchard
Assignee: Siliconix Incorporated
Title: "PLANAR VERTICAL CHANNEL DMOS STRUCTURE"
Serial No.: 06/843,454 Filing Date: 03/24/86
Examiner: T. Thomas Art Unit: 114
Attorney Docket No.: M-300 US

Santa Clara, California
November 23, 1987

COMMISSIONER OF PATENTS & TRADEMARKS
Washington, D. C. 20231

AMENDMENT

Sir:

In response to the Office Action of June 22, 1987, please
amend the application as follows:

IN THE CLAIMS

Please amend the claims as follows:

1. ~~(Amended)~~ A method of making a semiconductor device
comprising the following steps:

1. forming a first region of a semiconductor material
having a first conductivity type;

2. forming a second region of a semiconductor material
having a second conductivity type above and in contact
with said first region, said second region having a top
surface;

3. forming a third region of said first conductivity
type in a first portion of said second region, said third
region extending to a first portion of said top surface;

4. forming a first [rectangular] groove in said first
portion of said top surface, said first [rectangular]

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